

## Product Summary

$BV_{DSS}$	$R_{DS(ON)}$ Max	$I_D$ Max $T_A = +25^\circ C$
300V	4.0Ω @ $V_{GS} = 10V$	0.43A
	5.0Ω @ $V_{GS} = 4.5V$	0.39A

## Description

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) yet maintain superior switching performance, which makes the device ideal for high-efficiency power-management applications.

## Applications

- DC-DC Converters
- Power-Management Functions
- Battery-Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, and so on

## Features and Benefits

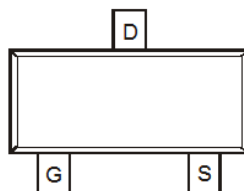
- Low Gate-Threshold Voltage
- Low-Input Capacitance
- Fast-Switching Speed
- Small Surface-Mount Package
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

## Mechanical Data

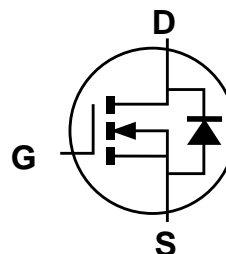
- Case: SOT23
- Case Material: Molded Plastic; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminals: Solderable per MIL-STD-202, Method 208  
Lead-Free Plating—Matte Tin Finish Annealed over Alloy 42 Leadframe (E3)
- Terminal Connections—See Diagram
- Weight: 0.008 grams (Approximate)



Top View



Top View  
Pin Configuration



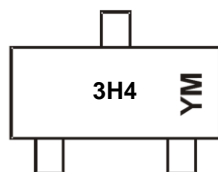
Equivalent Circuit

## Ordering Information (Note 4)

Part Number	Case	Packaging
DMN30H4D1S-7	SOT23	3,000/Tape & Reel
DMN30H4D1S-13	SOT23	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



3H4 = Product Type Marking Code  
 YM = Date Code Marking  
 Y or  $\bar{Y}$  = Year (ex: F = 2018)  
 M = Month (ex: 9 = September)

### Date Code Key

Year	2018	2019	2020	2021	2022	2023	2024	2025
Code	F	G	H	I	J	K	L	M

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	300	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	0.43 0.34	A
Pulsed Drain Current (10µs Pulse, Duty Cycle ≤ 1%)			I <sub>DM</sub>	2	A
Maximum Body Diode Continuous Current (Note 6)			I <sub>S</sub>	1.3	A
Pulsed Source Current (10µs Pulse, Duty Cycle ≤ 1%)			I <sub>SM</sub>	2	A

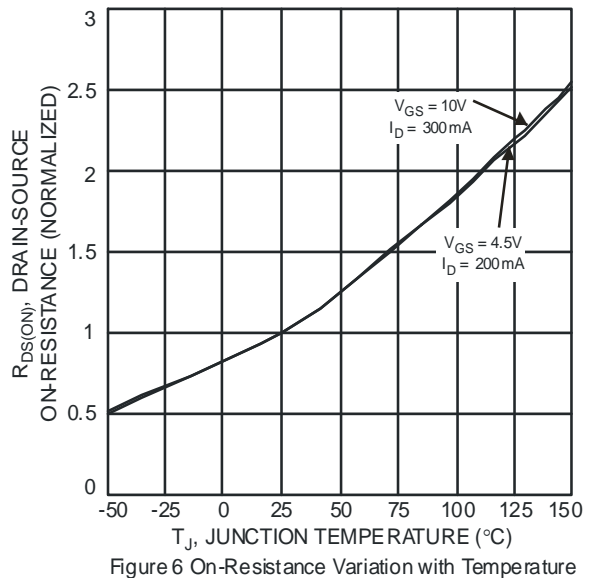
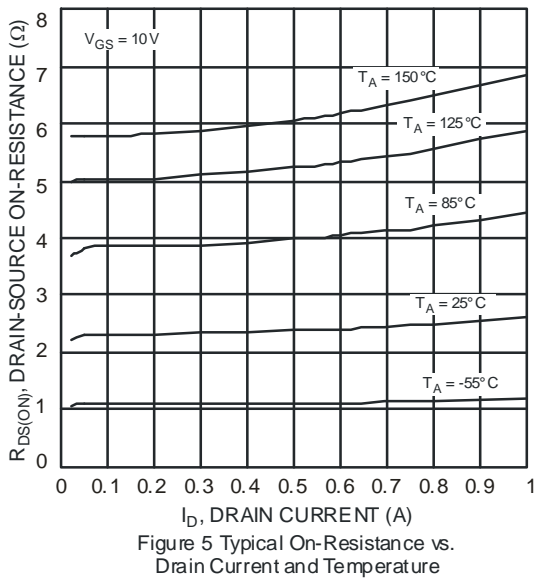
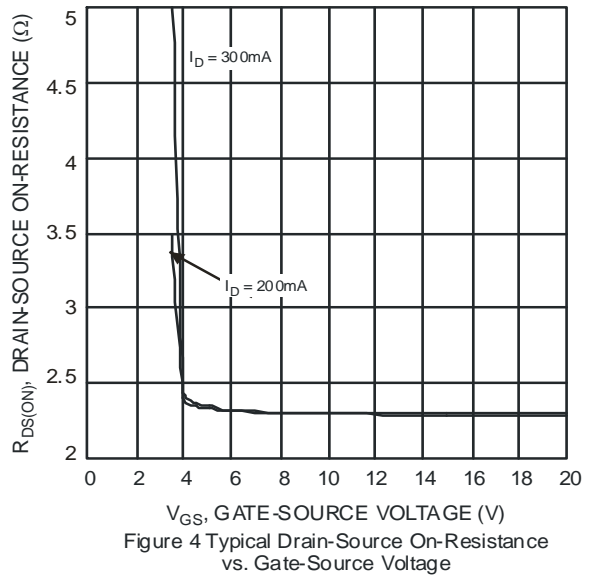
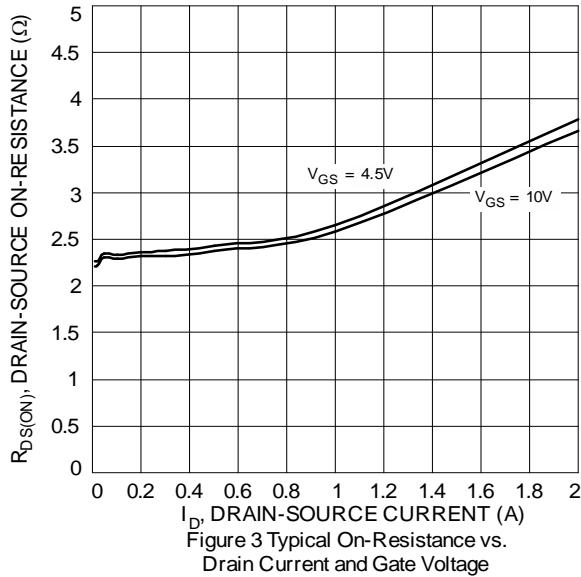
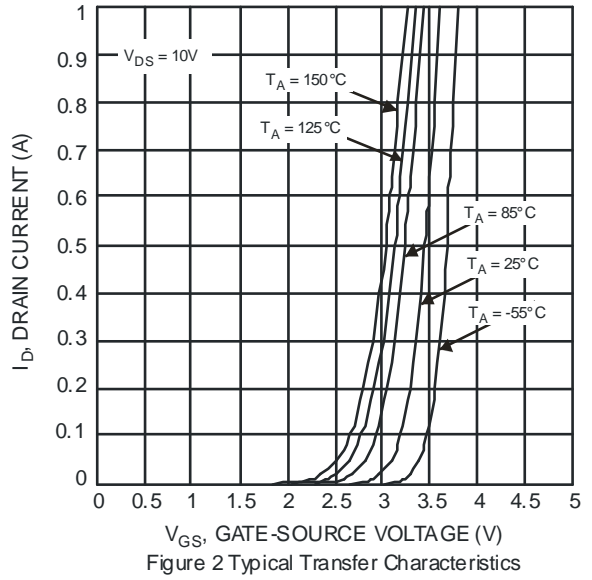
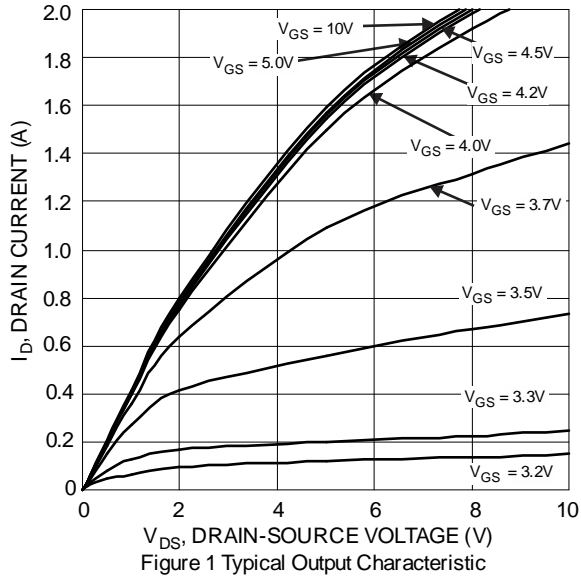
**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Total Power Dissipation (Note 5)			P <sub>D</sub>	0.36	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		R <sub>θJA</sub>	162	°C/W
Total Power Dissipation (Note 6)			P <sub>D</sub>	0.43	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		R <sub>θJA</sub>	111	°C/W
Thermal Resistance, Junction to Case (Note 6)			R <sub>θJC</sub>	31	°C/W
Operating and Storage Temperature Range			T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	300	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1.0	µA	V <sub>DS</sub> = 240V, V <sub>GS</sub> = 0V
Gate-Body Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	—	3	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	2.29	4.0	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.3A
		—	2.34	5.0		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 0.2A
Diode Forward Voltage	V <sub>SD</sub>	—	0.7	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 0.3A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iSS</sub>	—	174	—	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	12	—		
Reverse Transfer Capacitance	C <sub>rSS</sub>	—	7	—		
Gate Resistance	R <sub>g</sub>	—	2.96	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge	Q <sub>g</sub>	—	4.8	—	nC	V <sub>DS</sub> = 192V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.5A
Gate-Source Charge	Q <sub>gs</sub>	—	0.6	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	2.1	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	6.1	—	ns	V <sub>DS</sub> = 60V, R <sub>L</sub> = 200Ω V <sub>GS</sub> = 10V, R <sub>G</sub> = 25Ω
Turn-On Rise Time	t <sub>R</sub>	—	3.5	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	20.6	—		
Turn-Off Fall Time	t <sub>F</sub>	—	13.8	—		
Reverse Recovery Time	t <sub>RR</sub>	—	43	—	ns	I <sub>F</sub> = 0.5A, di/dt = 100A/µs
Reverse Recovery Charge	Q <sub>RR</sub>	—	51	—	nC	

- Notes:
- Device mounted on FR-4 PC board with minimum recommended pad layout, single sided.
  - Device mounted on FR-4 substrate PC board, 2oz copper with 1-inch square copper pad layout.
  - Short-duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to production testing.



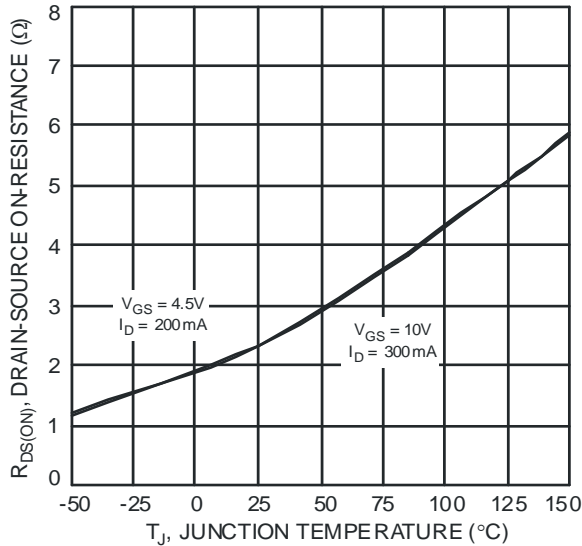


Figure 7 On-Resistance Variation with Temperature

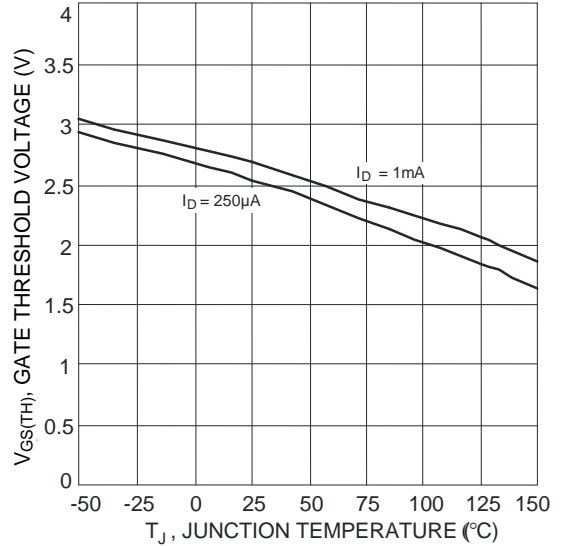


Figure 8 Gate Threshold Variation vs. Junction Temperature

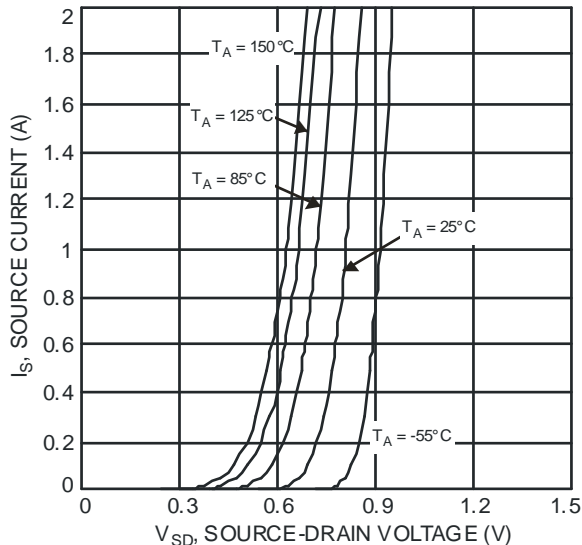


Figure 9 Diode Forward Voltage vs. Current

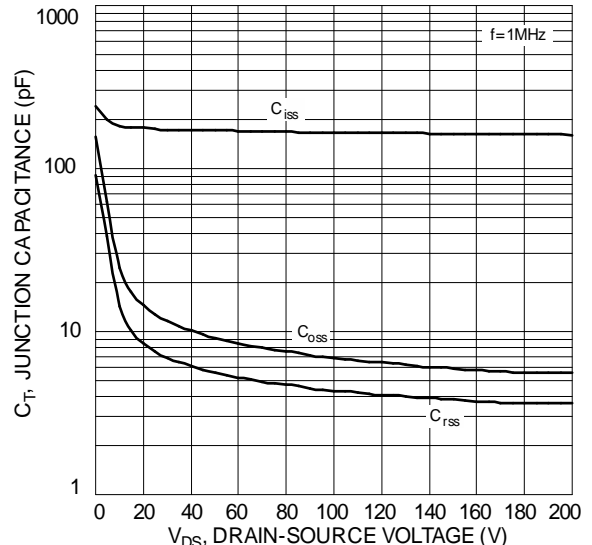


Figure 10 Typical Junction Capacitance

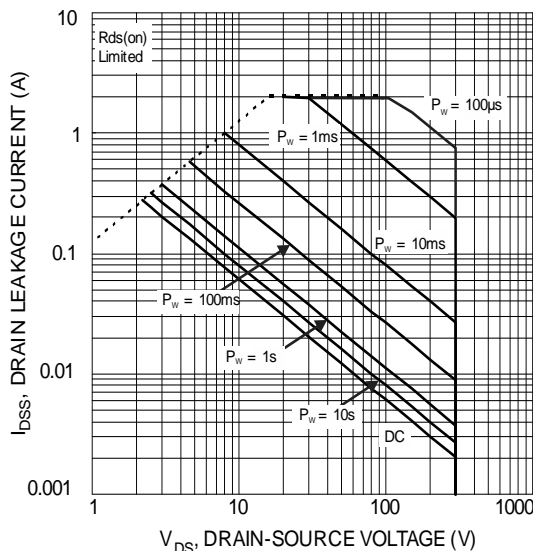


Figure 10 Typical Drain-Source Leakage Current vs. Voltage

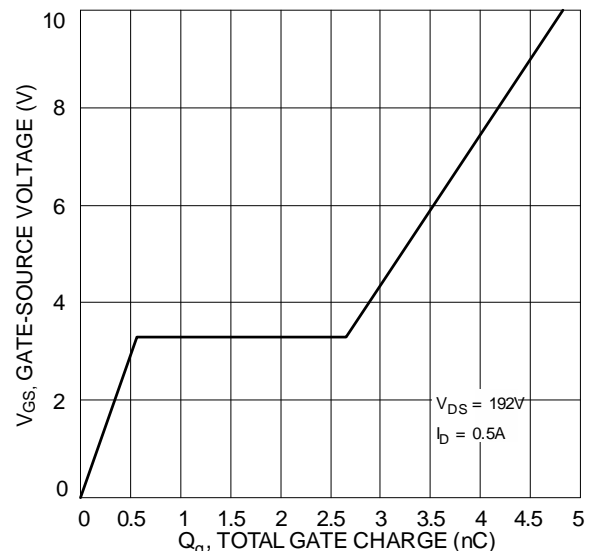
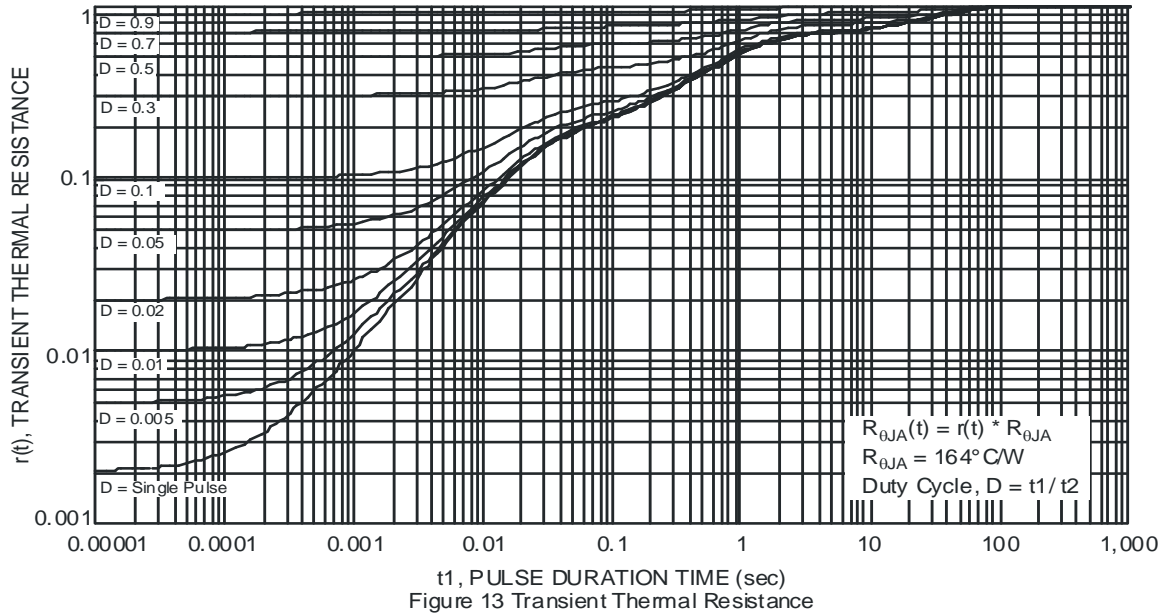


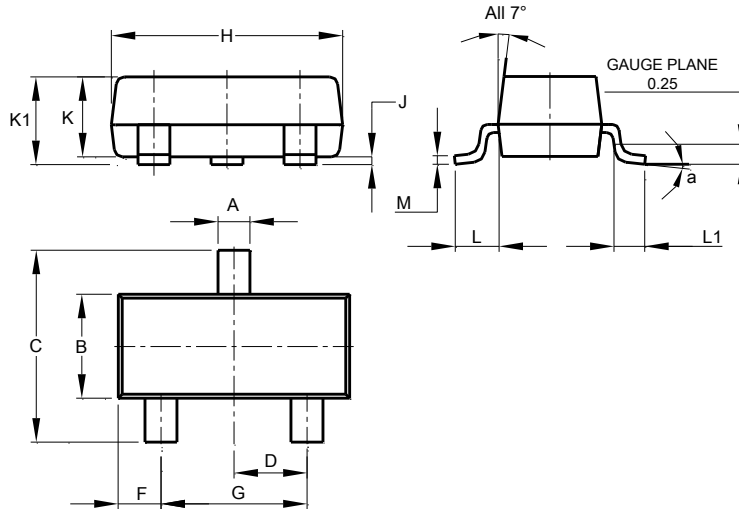
Figure 12 Gate Charge



**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT23**

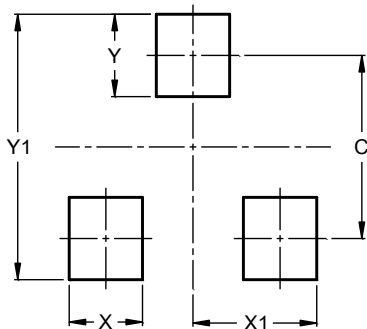


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT23**



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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